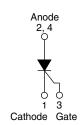
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Thyristor, Surface Mount, Phase Control SCR, 16 A





D²PAK (TO-263AB)

PRIMARY	CHARACTERISTICS

I _{T(AV)}	16 A			
V _{DRM} /V _{RRM}	800 V, 1200 V			
V_{TM}	1.25 V			
I _{GT}	45 mA			
T_J	-40 to +125 °C			
Package	D ² PAK (TO-263AB)			
Circuit configuration	Single SCR			

FEATURES

 Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C

 Designed and qualified according JEDEC®-JESD 47 ROHS COMPLIANT HALOGEN FREE

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- · Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

DESCRIPTION

The VS-25TTS...S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS									
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS									
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5							
Aluminum IMS, R _{thCA} = 15 °C/W	8.5	13.5	А						
Aluminum IMS with heatsink, R _{thCA} = 5 °C/W	16.5	25.0							

Note

• $T_A = 55$ °C, $T_J = 125$ °C, footprint 300 mm²

MAJOR RATINGS	MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS							
I _{T(AV)}	Sinusoidal waveform	16	Α							
I _{RMS}		25	^							
V _{RRM} /V _{DRM}		800 to 1200	V							
I _{TSM}		350	А							
V _T	16 A, T _J = 25 °C	1.25	V							
dV/dt		500	V/µs							
dl/dt		150	A/µs							
T _J		-40 to +125	°C							

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} /I _{DRM} , AT 125 °C mA						
VS-25TTS08S-M3	800	800	10						
VS-25TTS12S-M3	1200	1200]						



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ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEC	T CONDITIONS	VAL	UES	UNITS		
PARAMETER	STINIBUL	SYMBOL TEST CONDITIONS				UNITS		
Maximum average on-state current	I _{T(AV)}	T _C = 93 °C, 180° c	onduction half sine wave	1	6			
Maximum RMS on-state current	I _{RMS}			2	:5	Α		
Maximum peak, one-cycle,	ı	10 ms sine pulse,	rated V _{RRM} applied	30	00	_ ^		
non-repetitive surge current	I _{TSM}	10 ms sine pulse,	no voltage reapplied	3	50	1		
Maximum 12t fax fusing	l ² t	10 ms sine pulse,	rated V _{RRM} applied	450		A ² s		
Maximum I ² t for fusing	1-1	10 ms sine pulse,	630		A-S			
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 10 m	t = 0.1 ms to 10 ms, no voltage reapplied			A²√s		
Maximum on-state voltage drop	V_{TM}	16 A, T _J = 25 °C	16 A, T _J = 25 °C			V		
On-state slope resistance	r _t	$\frac{r_t}{r_t}$ $T_J = 125 ^{\circ}\text{C}$		2.0	mΩ			
Threshold voltage	V _{T(TO)}	TO) 1J = 125 G		.0	V			
Maximum various and direct leakage arrayant	1 //	T _J = 25 °C	W roted W A/	0	.5			
Maximum reverse and direct leakage current	I _{RM} /I _{DM}	T _J = 125 °C	V_R = rated V_{RRM}/V_{DRM}	10				
Holding current	I _H	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C	-	150	mA		
Maximum latching current	ΙL	Anode supply = 6 V, resistive load, T _J = 25 °C			00			
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J$ max., linear to 80 %, $V_{DRM} = R_g - k = open$			00	V/µs		
Maximum rate of rise of turned-on current	dl/dt				150			

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}		8.0	W
Maximum average gate power	P _{G(AV)}		2.0	VV
Maximum peak positive gate current	+ I _{GM}		1.5	Α
Maximum peak negative gate voltage	- V _{GM}		10	V
		Anode supply = 6 V, resistive load, T _J = - 10 °C		
Maximum required DC gate current to trigger	I _{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	45	mA
		Anode supply = 6 V, resistive load, T _J = 125 °C	20	
		Anode supply = 6 V, resistive load, T _J = - 10 °C	2.5	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T _J = 25 °C	2.0	V
		Anode supply = 6 V, resistive load, T _J = 125 °C	1.0	V
Maximum DC gate voltage not to trigger	V_{GD}	T 105 °C V reted value	0.25	
Maximum DC gate current not to trigger	I_{GD}	T _J = 125 °C, V _{DRM} = rated value	2.0	mA

SWITCHING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Typical turn-on time	t _{gt}	T _J = 25 °C	0.9					
Typical reverse recovery time	t _{rr}	T 105 °C	4	μs				
Typical turn-off time	tq	T _J = 125 °C	110					

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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
Maximum junction and storage temperature range	T _J , T _{Stg}		-40 to +125	°C					
Maximum thermal resistance, junction to case	R _{thJC}	R _{thJC} DC operation		°C/W					
Typical thermal resistance, junction to ambient (PCB mount)	R _{thJA} ⁽¹⁾		40	C/VV					
Approximate weight			2	g					
Approximate weight			0.07	OZ.					
Marking daying		Case style D ² PAK (TO-263AB)	25TTS08S						
Marking device		Case style D-PAR (10-203AB)	25TTS12S						

Note

⁽¹⁾ When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140 µm] copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

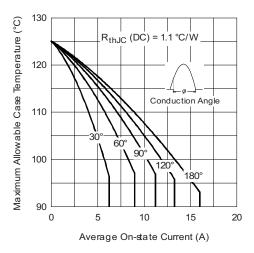


Fig. 1 - Current Rating Characteristics

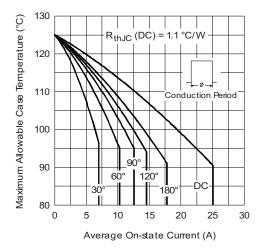


Fig. 2 - Current Rating Characteristics

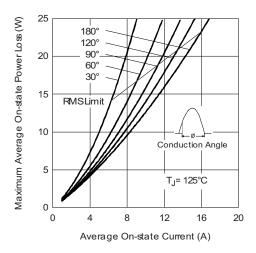


Fig. 3 - On-State Power Loss Characteristics

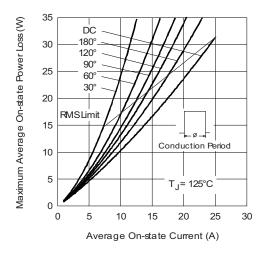


Fig. 4 - On-State Power Loss Characteristics

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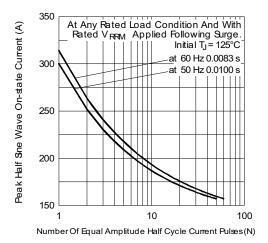


Fig. 5 - Maximum Non-Repetitive Surge Current

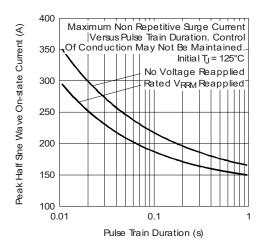


Fig. 6 - Maximum Non-Repetitive Surge Current

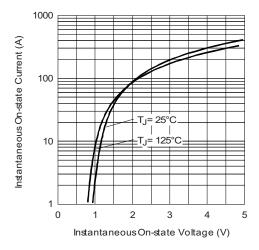


Fig. 7 - On-State Voltage Drop Characteristics

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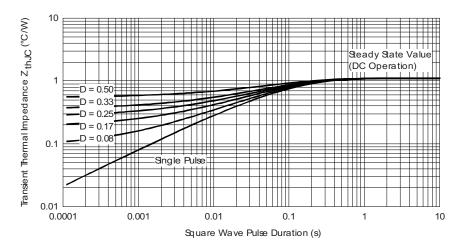


Fig. 8 - Gate Characteristics

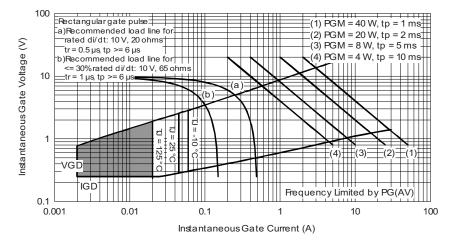
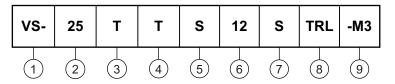


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE

Device code



- Vishay Semiconductors product
- 2 Current rating (25 = 25 A)
- Gircuit configuration:

 T = single thyristor
- 4 Package:
 - $T = D^2PAK (TO-263AB)$
- **5** Type of silicon:
- S = standard recovery rectifier 08 = 800 V

 Voltage rating: voltage code x 100 = V_{RRM} 12 = 1200 V
- 7 S = surface mountable
- 8 • None = tube
 - TRL = tape and reel (left oriented)
 - TRR = tape and reel (right oriented)
- 9 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-25TTS08S-M3	50	Antistatic plastic tubes							
VS-25TTS08STRL-M3	800	13" diameter plastic tape and reel							
VS-25TTS08STRR-M3	800	13" diameter plastic tape and reel							
VS-25TTS12S-M3	50	Antistatic plastic tubes							
VS-25TTS12STRL-M3	800	13" diameter plastic tape and reel							
VS-25TTS12STRR-M3	800	13" diameter plastic tape and reel							

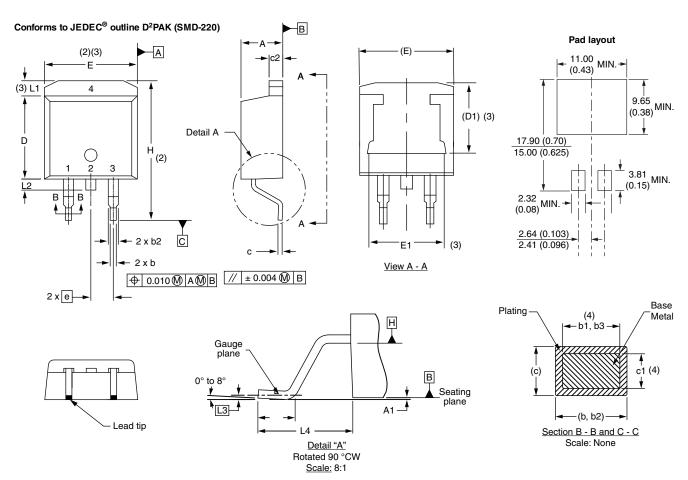
LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?96164</u>							
Part marking information	www.vishay.com/doc?95444						
Packaging information	www.vishay.com/doc?96424						



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES	NOTES		MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

Revision: 13-Jul-17 Document Number: 96164



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